TOSHIBA Transistor Silicon PNP Triple Diffused Type (PCT process)

2SA1200

High Voltage Switching Applications

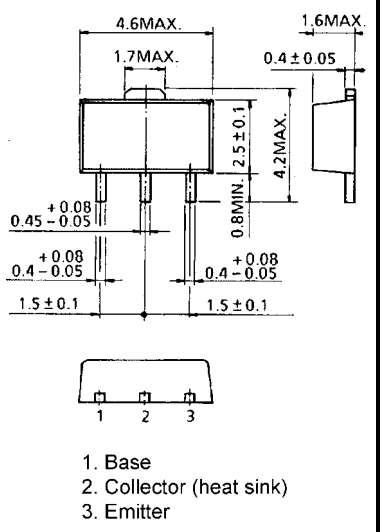
- High voltage: V_{CEO} = −150 V
- High transition frequency: f_T = 120 MHz (typ.)
- Small flat package
- P_C = 1 to 2 W (mounted on ceramic substrate)
- Complementary to 2SC2880

Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	−150	V
Collector-emitter voltage	V_{CEO}	−150	V
Emitter-base voltage	V_{EBO}	−5	V
Collector current	I_C	−50	mA
Base current	I_B	−10	mA
Collector power dissipation	P_C	500	mW
	P_C (Note 1)	800	
Junction temperature	T_j	150	°C
Storage temperature range	T_{stg}	−55 to 150	°C

Note 1: 2SA1200 mounted on ceramic substrate (250 mm^2 × 0.8 t)

Unit: mm



1. Base
2. Collector (heat sink)
3. Emitter

PW-MINI	
JEDEC	—
JEITA	SC-62
TOSHIBA	2-5K1A

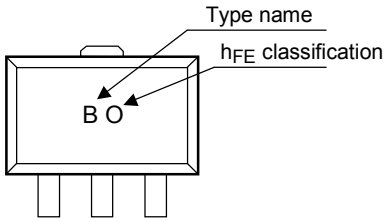
Weight: 0.05 g (typ.)

Electrical Characteristics (Ta = 25°C)

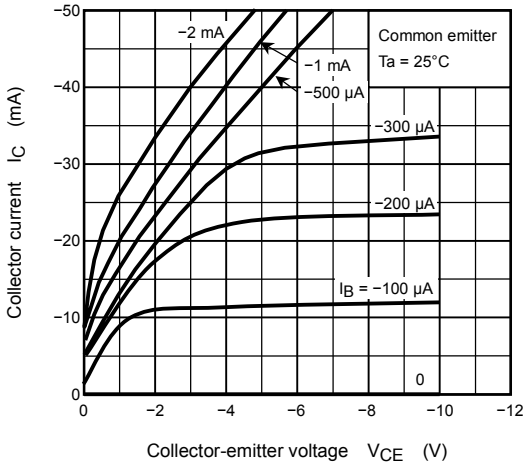
Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current	I_{CBO}	V_{CB} = −150 V, I_E = 0	—	—	−0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB} = −5 V, I_C = 0	—	—	−0.1	μA
DC current gain	h_{FE} (Note 2)	V_{CE} = −5 V, I_C = −10 mA	70	—	240	
Collector-emitter saturation voltage	$V_{CE\ (sat)}$	I_C = −10 mA, I_B = −1 mA	—	—	−0.8	V
Base-emitter voltage	V_{BE}	V_{CE} = −5 V, I_C = −30 mA	—	—	−0.9	V
Transition frequency	f_T	V_{CE} = −30 V, I_C = −10 mA	—	120	—	MHz
Collector output capacitance	C_{ob}	V_{CB} = −10 V, I_E = 0, f = 1 MHz	—	4.0	5.0	pF

Note 2: h_{FE} classification O: 70 to 140, Y: 120 to 240

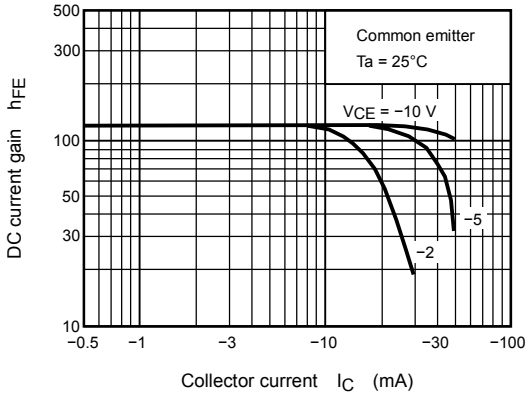
Marking



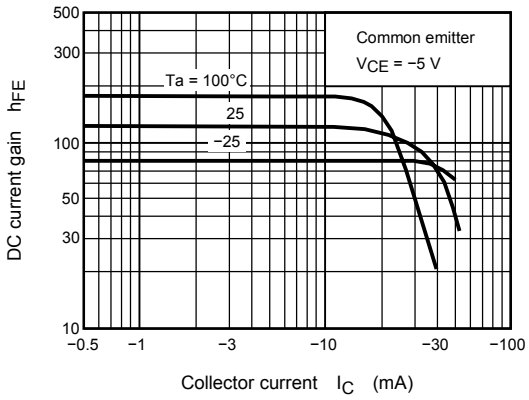
$I_C - V_{CE}$



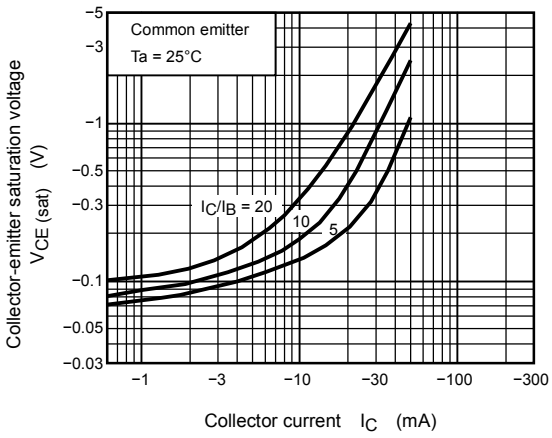
$h_{FE} - I_C$



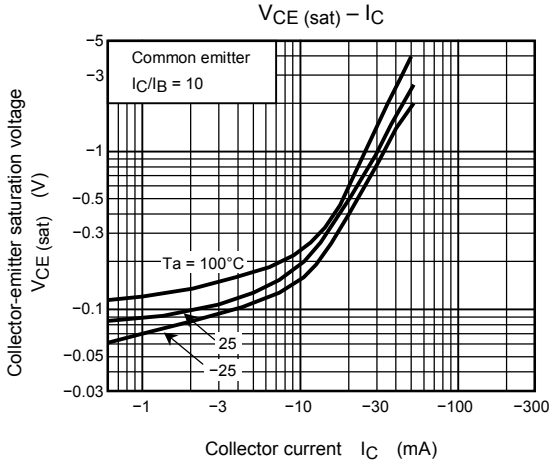
$h_{FE} - I_C$



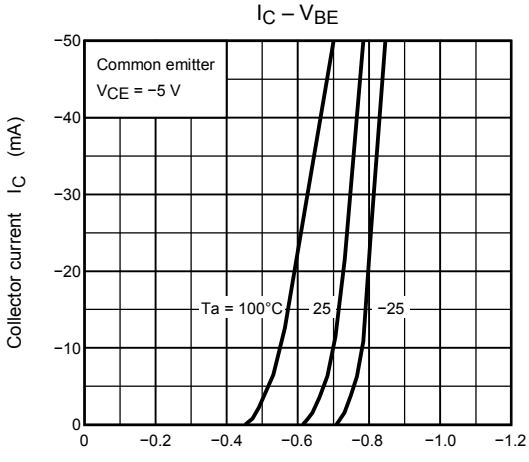
$V_{CE\ (sat)} - I_C$



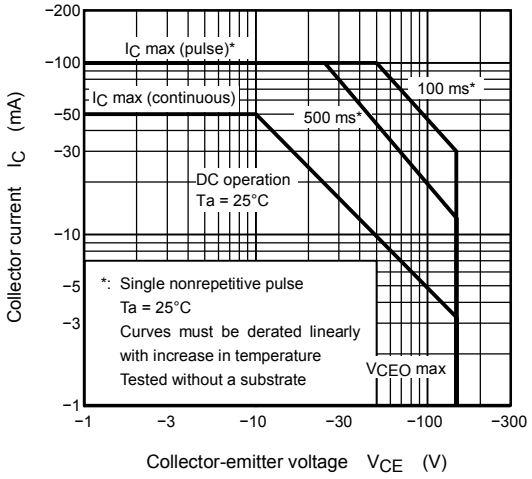
$V_{CE\ (sat)} - I_C$



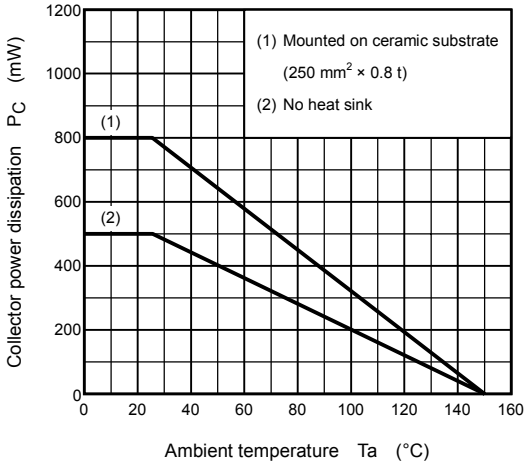
$I_C - V_{BE}$



Safe Operating Area



P_C – Ta



RESTRICTIONS ON PRODUCT USE

000707EAA

- TOSHIBA is continually working to improve the quality and reliability of its products. Nevertheless, semiconductor devices in general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the buyer, when utilizing TOSHIBA products, to comply with the standards of safety in making a safe design for the entire system, and to avoid situations in which a malfunction or failure of such TOSHIBA products could cause loss of human life, bodily injury or damage to property.
  In developing your designs, please ensure that TOSHIBA products are used within specified operating ranges as set forth in the most recent TOSHIBA products specifications. Also, please keep in mind the precautions and conditions set forth in the “Handling Guide for Semiconductor Devices,” or “TOSHIBA Semiconductor Reliability Handbook” etc..
- The TOSHIBA products listed in this document are intended for usage in general electronics applications (computer, personal equipment, office equipment, measuring equipment, industrial robotics, domestic appliances, etc.). These TOSHIBA products are neither intended nor warranted for usage in equipment that requires extraordinarily high quality and/or reliability or a malfunction or failure of which may cause loss of human life or bodily injury (“Unintended Usage”). Unintended Usage include atomic energy control instruments, airplane or spaceship instruments, transportation instruments, traffic signal instruments, combustion control instruments, medical instruments, all types of safety devices, etc.. Unintended Usage of TOSHIBA products listed in this document shall be made at the customer’s own risk.
- The information contained herein is presented only as a guide for the applications of our products. No responsibility is assumed by TOSHIBA CORPORATION for any infringements of intellectual property or other rights of the third parties which may result from its use. No license is granted by implication or otherwise under any intellectual property or other rights of TOSHIBA CORPORATION or others.
- The information contained herein is subject to change without notice.